

2N 5179

SILICON PLANAR NPN

VHF/UHF AMPLIFIER

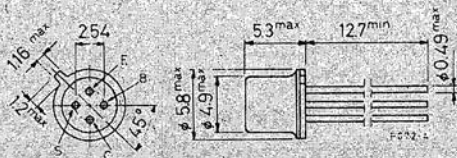
The 2N 5179 is a silicon planar epitaxial NPN transistor in Jedec TO-72 metal case, intended for low-noise tuned-amplifier and converter applications up to 500 MHz.

ABSOLUTE MAXIMUM RATINGS

V_{CB0}	Collector-base voltage ($I_E = 0$)	20	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	12	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	2.5	V
I_C	Collector current	50	mA
P_{tot}	Total power dissipation at $T_{amb} \leq 25^\circ\text{C}$	200	mW
	at $T_{case} \leq 25^\circ\text{C}$	300	mW
T_{stg}, T_j	Storage and junction temperature	-65 to 200	$^\circ\text{C}$

MECHANICAL DATA

Dimensions in mm



(sim. to TO-72)

THERMAL DATA

$R_{th \text{ j-case}}$	Thermal resistance junction-case	max	583	°C/W
$R_{th \text{ j-amb}}$	Thermal resistance junction-ambient	max	875	°C/W

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter		Test conditions		Min.	Typ.	Max.	Unit
I_{CBO}	Collector cutoff current ($I_E = 0$)	$V_{CB} = 15\text{V}$ $V_{CB} = 15\text{V}$	$T_{amb} = 150^{\circ}\text{C}$			20 1	nA μA
$V_{(BR)CBO}$	Collector-base breakdown voltage ($I_E = 0$)	$I_C = 1 \mu\text{A}$		20			V
$V_{CEO(sus)}$	Collector-emitter sustaining voltage ($I_B = 0$)	$I_C = 3 \text{mA}$		12			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage ($I_C = 0$)	$I_E = 10 \mu\text{A}$		2.5			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 10 \text{mA}$	$I_B = 1 \text{mA}$			0.4	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = 10 \text{mA}$	$I_B = 1 \text{mA}$			1	V
h_{FE}	DC current gain	$I_C = 3 \text{mA}$	$V_{CE} = 1\text{V}$	25	70	250	—
h_{fe}	Small signal current gain	$I_C = 2 \text{mA}$ $f = 1 \text{kHz}$	$V_{CE} = 6\text{V}$	25	90	300	—
f_T	Transition frequency	$I_C = 5 \text{mA}$ $f = 100 \text{MHz}$	$V_{CE} = 6\text{V}$	0.9	1.4	2	GHz
$-C_{re}$	Reverse capacitance	$I_C = 0$ $f = 1 \text{MHz}$	$V_{CE} = 6\text{V}$		0.7	1	pF
NF	Noise figure	$I_C = 1.5 \text{mA}$ $f = 200 \text{MHz}$	$V_{CE} = 6\text{V}$ $R_g = 125 \Omega$		3	4.5	dB
G_{pe}	Power gain (neutralized)	$I_C = 5 \text{mA}$ $f = 200 \text{MHz}$	$V_{CE} = 12\text{V}$ $R_g = 50 \Omega$	15	21		dB
P_o	Oscillator power output	$I_C = 12 \text{mA}$ $f = 500 \text{MHz}$	$V_{CB} = 10\text{V}$	20			mW
$\tau_{bb} C_{bc}$	Feedback time constant	$I_C = 2 \text{mA}$ $f = 31.9 \text{MHz}$	$V_{CB} = 6\text{V}$	3	7	14	ps